



Micro Commercial Components  
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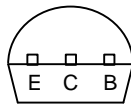
## 2SA1015

### PNP Silicon Plastic-Encapsulate Transistor

### Features

- Capable of 0.4Watts of Power Dissipation.
- Collector-current 0.15A
- Collector-base Voltage 50V
- Operating and storage junction temperature range: -55°C to +150°C

Pin Configuration  
 Bottom View



### Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emmitter Breakdown Voltage ( $I_C=0.1mA_{dc}$ , $I_E=0$ )	50	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_C=100\mu A_{dc}$ , $I_E=0$ )	50	---	Vdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB}=50V_{dc}$ , $I_E=0$ )	---	0.1	$\mu A_{dc}$
$I_{EBO}$	Emmitter Cutoff Current ( $V_{EB}=5.0V_{dc}$ , $I_C=0$ )	---	0.1	$\mu A_{dc}$

### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain ( $I_C=2.0mA_{dc}$ , $V_{CE}=6.0V_{dc}$ )	70	400	---
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage ( $I_C=100mA_{dc}$ , $I_E=10mA_{dc}$ )	---	0.3	Vdc
$V_{BE(sat)}$	Base-Emmitter Saturation Voltage ( $I_C=100mA_{dc}$ , $I_E=10mA_{dc}$ )	---	1.1	Vdc
$V_{BE}$	Base-Emmitter Voltage ( $I_E=310mA_{dc}$ )	---	1.45	Vdc

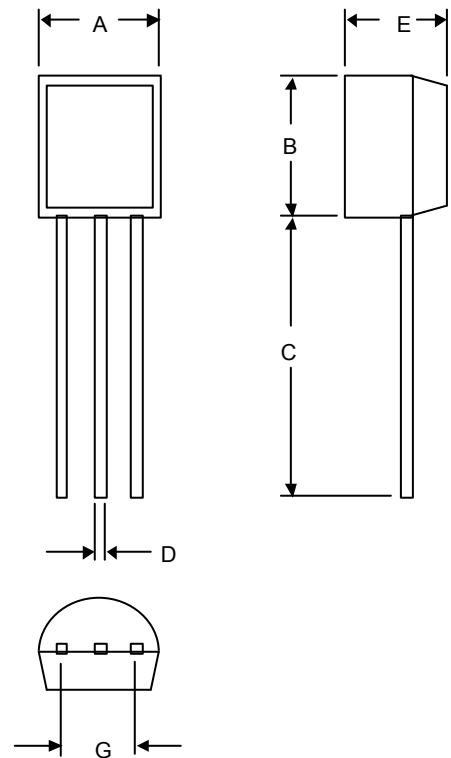
### SMALL-SIGNAL CHARACTERISTICS

$f_T$	Transistor Frequency ( $I_C=1.0mA_{dc}$ , $V_{CE}=10V_{dc}$ , $f=30MHz$ )	80	---	MHz
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### CLASSIFICATION OF $h_{FE}$ (1)

Rank	O	Y	GR
Range	70-140	120-240	200-400

### TO-92



DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	